

SEMICONDUCTOR STRUCTURE AND METHOD FOR MANUFACTURING SAME

ABSTRACT

A semiconductor structure and a method for manufacturing same are provided. The semiconductor structure includes: a doped conductive layer, doped with dopant ions; a metal conductive layer, located above the doped conductive layer; a nitrogen-containing dielectric layer, located above the metal conductive layer; a first molybdenum nitride layer, located between the doped conductive layer and the metal conductive layer and configured to be electrically connected to the doped conductive layer and the metal conductive layer; and a second molybdenum nitride layer, located between the metal conductive layer and the nitrogen-containing dielectric layer, where an atomic ratio of nitrogen atoms in the second molybdenum nitride layer is greater than an atomic ratio of nitrogen atoms in the first molybdenum nitride layer. The embodiments of this disclosure are conducive to improving the conductive performance of the metal conductive layer.

[Fig. 1]